

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	437110	MEM (micromechanic\$2 microelectromechanic\$2) adj (structure component element)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:06
L2	2080	(micromechanic\$2 microelectromechanic\$2) adj (structure component element)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:06
L3	162	2 and (membrane adj layer second adj sacrificial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:07
L4	1614	micromechanical adj (structure component element)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:07
L5	134	L4 and (membrane adj layer second adj sacrificial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:07
L6	28	3 not L5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:14
L7	1692	2 and (electroconductive adj layer conductive layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:26
L8	30	7 and (HF near etch hydrogen adj fluoroide with etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 13:14
L9	240	2 and (electroconductive adj layer conductive adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:26

L10	3	9 and (HF near etch hydrogen adj fluoroide with etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:31
L11	165	9 and (silicon adj oxide silicon adj dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 10:40
L12	2	("20030001221").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/04/01 10:45
L13	2	("20040065932").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/04/01 12:51
L14	1	2002-149019.NRAN.	DERWENT	OR	ON	2005/04/01 10:46
L15	1	("19940512").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/04/01 13:01
L16	2	("20040112937").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/04/01 13:01
L17	1	2002-464416.NRAN.	DERWENT	OR	ON	2005/04/01 13:02
L18	38	(HF near etch hydrogen adj fluoroide with etch hydrofluoric with etch) and silicon adj nitride and silicon near content	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 13:44
L19	2	("20030141561").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/04/01 13:44
S1	6342	micromechanical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/30 15:50

S2	1146	S1 and sacrificial adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/30 15:51
S3	126	S2 and movable adj element	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/30 15:51
S4	2374	(257/415,417,418,419).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/31 09:55
S5	1726	S4 and @ad<"20020713"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/31 09:56
S6	132	S5 and insulat\$3 and sacrificial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/31 10:01
S7	100	S5 and insulat\$3 and micromechanical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/31 10:50
S8	1614	micromechanical adj (structure component element)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:04
S9	350	S8 and (silicon adj oxide silicon adj dioxide) and (silicon adj nitride silicon adj carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/31 11:19
S10	231	S9 and (movable adj element sacrificial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/31 12:00
S11	94	S8 and (movable adj element sacrificial) and etch adj stop	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/31 12:00

S12	74	S8 and HF! near etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/31 16:21
S13	134	S8 and (membrane adj layer second adj sacrificial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/01 08:06
S14	2	("20040248344").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/31 16:29